

KS54AHCT
KS74AHCT
164
8-Bit Serial-In/Parallel-Out Shift Registers

T-4609-05

FEATURES

- AND—Gated (enable/disable) serial inputs
- Fully buffered clock and serial inputs
- Direct clear
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- High-Drive-Current outputs:
 $I_{OL} = 8 \text{ mA} @ V_{OL} = 0.5 \text{ V}$
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
 KS74AHCT: -40°C to $+85^{\circ}\text{C}$
 KS54AHCT: -55°C to $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

DESCRIPTION

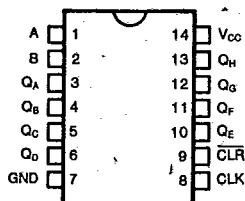
These are high-speed 8-bit registers with AND-gated serial inputs and an asynchronous clear. Data is entered serially through either one of the two inputs, A and B. A high on one input enables the other one, which will then determine the state of the first flip-flop. A low at either or both inputs inhibits data entry and resets the first flip-flop to a low level at the next positive clock transition.

Data at the serial inputs may be changed while the clock is high or low, provided the minimum setup time requirements are met. Clocking occurs on the low-to-high-level transition of their clock input.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

PIN CONFIGURATION



FUNCTION TABLE

Inputs				Outputs		
CLR	CLK	A	B	QA	QB ... QH	
L	X	X	X	L	L	L
H	L	X	X	QA0	QB0	QH0
H	↑	H	H	H	QAn	QGn
H	↑	L	X	L	QAn	QGn
H	↑	X	L	L	QAn	QGn

H = high level (steady state), L = low level (steady state)

X = irrelevant (any input, including transitions)

↑ = transition from low to high level.

QA0, QB0, QH0 = the level of QA, QB or QH, respectively, before the indicate steady-state input conditions were established.

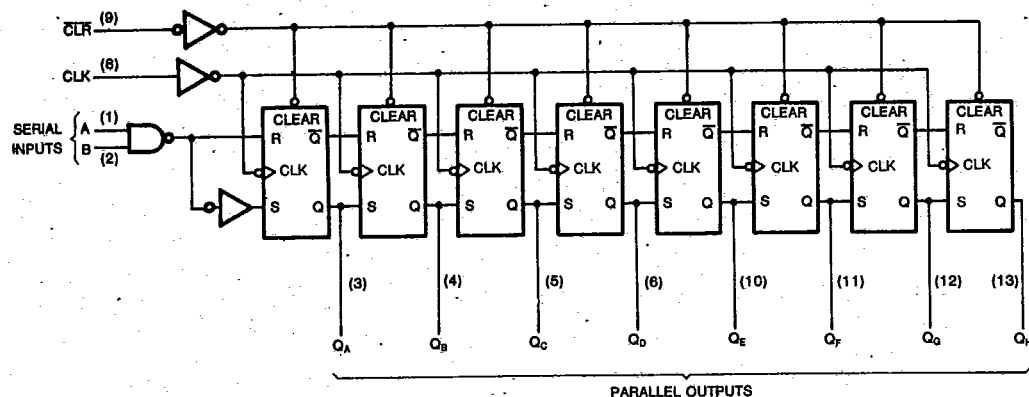
QAn, QGn = the level of QA or QG before the most-recent ↑ transition of the clock; indicates a one-bit shift.



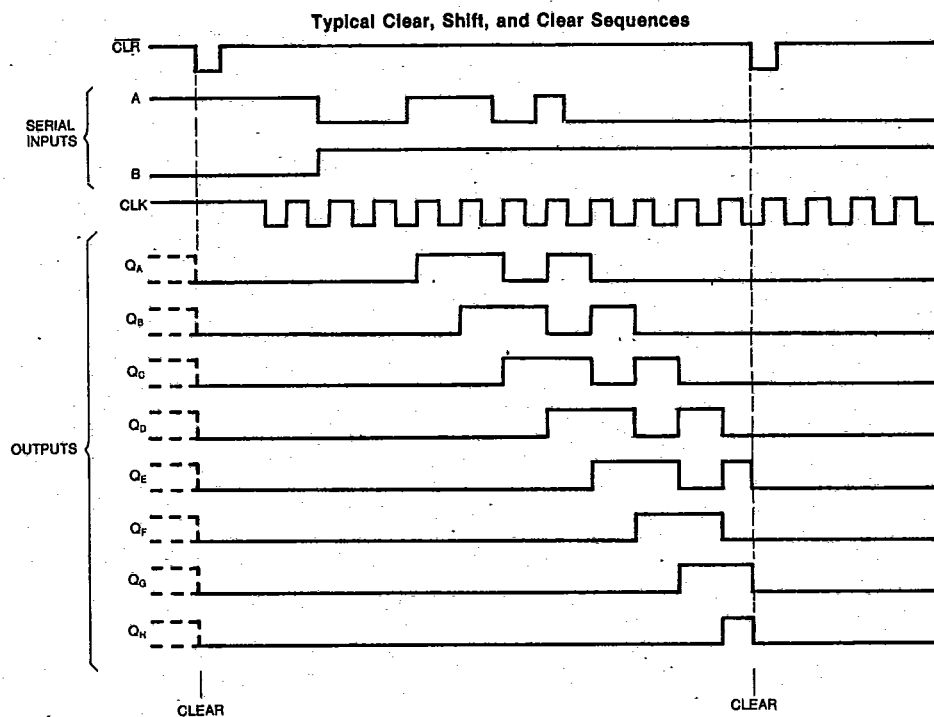
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KS54AHCT
KS74AHCT**164****8-Bit Serial-In/Parallel-Out Shift Registers**

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LOGIC DIAGRAMS

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KS54AHCT 164
KS74AHCT**8-Bit Serial-In/Parallel-Out Shift Registers****Absolute Maximum Ratings***

Supply Voltage Range V_{CC} -0.5V to +7V
 DC Input Diode Current, I_{IK}
 ($V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$) ± 20 mA
 DC Output Diode Current, I_{OK}
 ($V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$) ± 20 mA
 Continuous Output Current Per Pin, I_O
 ($-0.5V < V_O < V_{CC} + 0.5V$) ± 35 mA
 Continuous Current Through
 V_{CC} or GND pins ± 125 mA
 Storage Temperature Range, T_{stg} -65°C to +150°C
 Power Dissipation Per Package, P_d † 500 mW

* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:

Plastic Package (N): -12mW/°C from 65°C to 85°C
 Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

Supply Voltage, V_{CC} 4.5V to 5.5V
 DC Input & Output Voltages*, V_{IN} , V_{OUT} .. 0V to V_{CC}
 Operating Temperature

Range KS74AHCT: -40°C to +85°C
 KS54AHCT: -55°C to +125°C

Input Rise & Fall Times, t_r , t_f Max 500 ns

* Unused inputs must always be tied to an appropriate logic voltage level (either V_{CC} or GND)

DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$ Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	T _a = 25°C		KS74AHCT	KS54AHCT	Unit
					T _a = -40°C to +85°C	T _a = -55°C to +125°C	
			Typ	Guaranteed Limits			
Minimum High-Level Input Voltage	V _{IH}			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V _{IL}			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V _{OH}	V _{IN} =V _{IH} or V _{IL} I _O =-20μA I _O =-4mA	V _{CC} 4.2	V _{CC} -0.1 3.98	V _{CC} -0.1 3.84	V _{CC} -0.1 3.7	V
Maximum Low-Level Output Voltage	V _{OL}	V _{IN} =V _{IH} or V _{IL} I _O =20μA I _O =4mA I _O =8mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I _{IN}	V _{IN} =V _{CC} or GND		±0.1	±1.0	±1.0	μA
Maximum Quiescent Supply Current	I _{CC}	V _{IN} =V _{CC} or GND I _{OUT} =0μA		8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI _{CC}	per input pin V _I =2.4V other inputs: at V _{CC} or GND I _{OUT} =0μA		2.7	2.9	3.0	mA



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AC ELECTRICAL CHARACTERISTICS (Input t_r , $t_f \leq 2$ ns), AHCT164

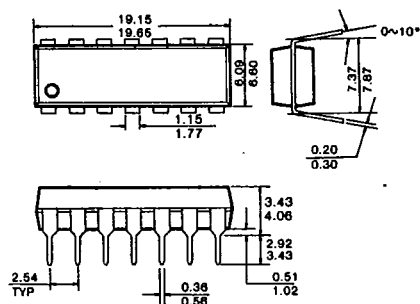
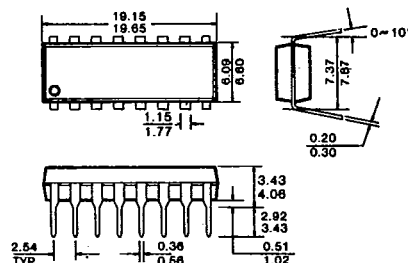
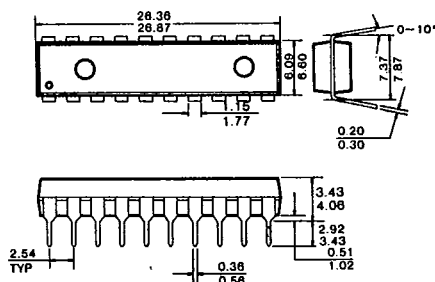
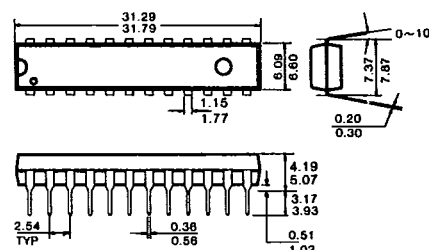
Characteristic	Symbol	Conditions†	$T_A = 25^\circ\text{C}$ $V_{CC} = 5.0\text{V}$	KS74AHCT $T_A = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		KS54AHCT $T_A = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		Unit
			Typ	Min	Max	Min	Max	
Maximum Clock Frequency	f_{max}	$C_L = 50\text{pF}$	60	36		30		MHz
Propagation Delay, CLR to any Q	t_{PHL}		12		20		24	ns
Propagation Delay, CLK to any Q	t_{PLH}		11		18		21	ns
	t_{PHL}		11		18		21	
Pulse Width	CLR Low	t_w	8	12		15		ns
	CLK High or Low		8	12		15		
Setup Time before CLK†	Data	t_{su}	8	12		15		ns
	CLR Inactive		8	12		15		
Hold Time Data after CLK†	t_h		1	4		5	6	ns
Input Capacitance	C_{IN}		5					pF
Power Dissipation Capacitance*	C_{PD}	(per package)	120					pF

* C_{PD} determines the no-load dynamic power dissipation: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

† For AC switching test circuits and timing waveforms see section 2.

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PACKAGE DIMENSIONS*T-90-20***1. PLASTIC PACKAGES****14-Pin Plastic DIP Units: mm****16-Pin Plastic DIP Units: mm****20-Pin Plastic DIP Units: mm****24-Pin Plastic DIP Units: mm**

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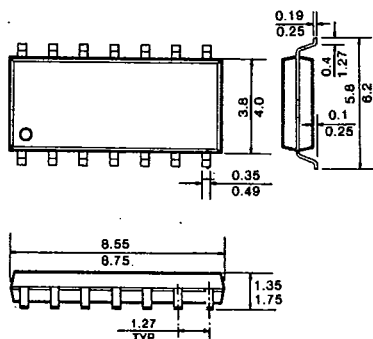
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PACKAGE DIMENSIONS

T-90-20

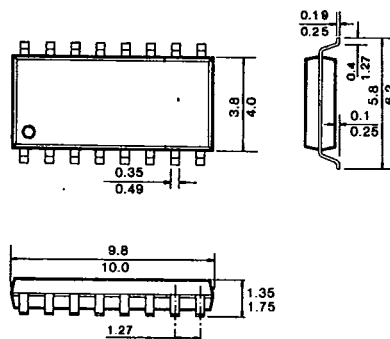
14-Pin SOP

Unit: mm



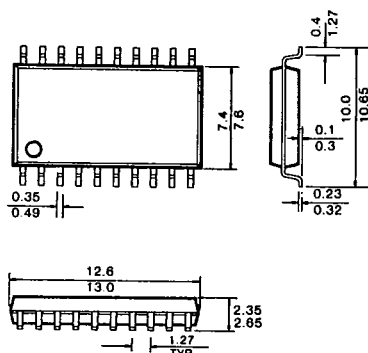
16-Pin SOP

Unit: mm



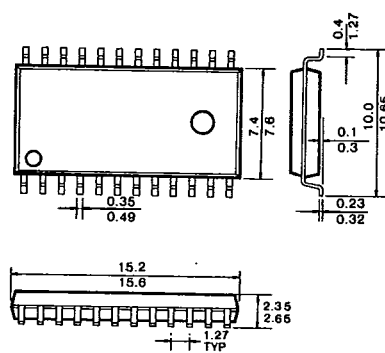
20-Pin SOP

Unit: mm



24-Pin SOP

Unit: mm



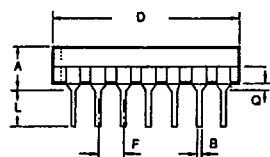
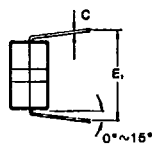
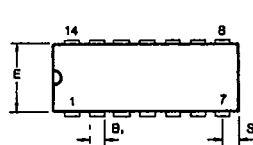
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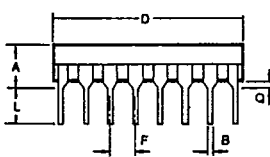
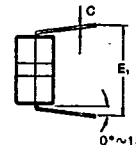
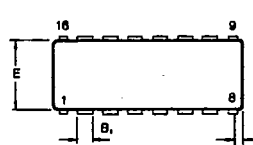
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PACKAGE DIMENSIONS

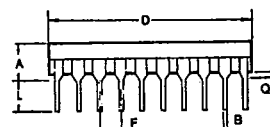
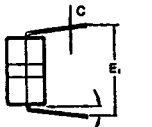
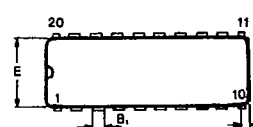
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2. CERAMIC PACKAGES**14-Pin Ceramic DIP Units: mm**

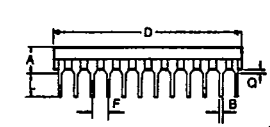
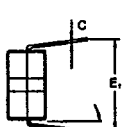
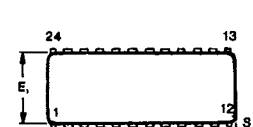
DIM	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	18.16	19.56
E	6.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	1.91	2.29

16-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	19.05	19.94
E	6.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	0.51	1.14

20-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	25.78	26.93
E	6.10	6.60
E ₁	7.77	7.95
F	2.54	
L	3.73	4.01
Q	0.38	0.89
S	0.51	1.14

24-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	31.50	32.84
E	7.24	7.75
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.508	1.776
S	1.85	1.93

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